

*CLAIM AMENDMENTS*

1. (Currently Amended) An interconnecting structure comprising:  
first wirings ~~on~~ supported by a substrate;  
a low-k dielectric film on the first wirings, the low-k dielectric film having a dielectric constant not exceeding 3;  
vias in a first portion of the low-k dielectric film and connected to the first wiring;  
second wirings in a second portion, further from the substrate than the first portion, of the low-k dielectric film, on the vias, and connected to the vias; and  
dummy vias in the first portion of the low-k dielectric film and on the periphery of an isolated via of the vias.
2. (Previously Presented) The interconnecting structure according to claim 1, further comprising a cap film on the low-k dielectric film, wherein the second wirings are in the cap film and the low-k dielectric film.
3. (Currently Amended) The interconnecting structure according to claim 1, further comprising:  
first dummy wirings on the periphery of the first wirings; and  
second dummy wirings on the periphery of the second wirings, wherein the dummy vias ~~is~~ are connected to the first and second dummy wirings, and one of the first and second dummy wirings connected to the dummy vias ~~are~~ is connected to ground potential.
4. (Original) The interconnecting structure according to claim 1, wherein the dummy vias have a slit shape.
5. (Currently Amended) The interconnecting structure according to claim 1, wherein the dummy vias have a dimension 1 to 10 times ~~a minimum dimension~~ one of the dimensions of the vias.
6. (New) The interconnecting structure according to claim 1, wherein the vias extend only in the first portion of the low-k dielectric film, and the dummy vias extend through both the first and second portions of the low-k dielectric film and do not contact the first wirings.

7. (New) The interconnecting structure according to claim 6, wherein the dummy vias have an opening dimension at the second portion of the low-k dielectric film no more than 10 times an opening dimension of the vias in the first portion of the low-k dielectric film.

8. (New) The interconnecting structure according to claim 1, wherein all of the first wirings, the vias, the second wirings, and the dummy vias have a damascene structure.

9. (New) An interconnecting structure comprising:  
first wirings supported by a substrate;  
a low-k dielectric film on the first wirings, the low-k dielectric film having a dielectric constant not exceeding 3;  
a cap film on the low-dielectric film;  
vias in the low-k dielectric film and in the cap film, the vias being connected to the first wiring;  
second wirings on the vias and connected to the vias, the second wiring having a surface coplanar with a surface of the cap film; and  
dummy vias on the periphery of an isolated via of the vias.

10. (New) The interconnecting structure according to claim 9, wherein all of the first wirings, the vias, the second wirings, and the dummy vias have a damascene structure.

11. (New) An interconnecting structure comprising:  
first wirings supported by a substrate;  
a low-k dielectric film on the first wirings, the low-k dielectric film having a dielectric constant not exceeding 3;  
vias in the low-k dielectric film and connected to the first wiring;  
second wirings on the vias and connected to the vias, the second wiring having a surface coplanar with a surface of the low-k dielectric film; and  
dummy vias on the periphery of an isolated via of the vias.

12. (New) The interconnecting structure according to claim 11, wherein all of the first wirings, the vias, the second wirings, and the dummy vias have a damascene structure.